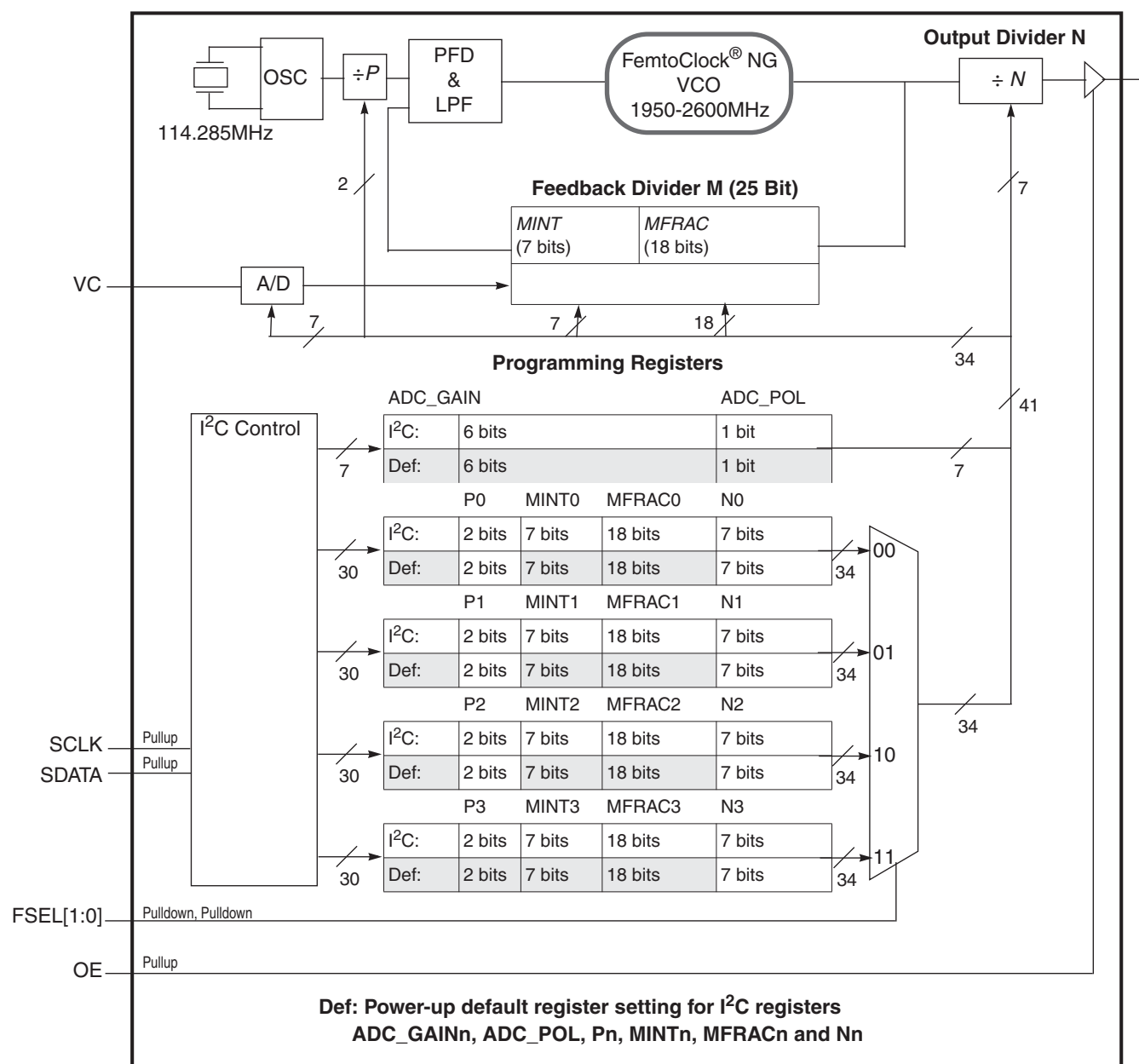


Block Diagram with Programming Registers



Pin Description and Characteristics

Table 1. Pin Descriptions

Number	Name	Type		Description
1	VC	Input		VCXO Control Voltage. The control voltage versus frequency characteristics are set by the ADC_GAIN[5:0] register bits.
2	OE	Input	Pullup	Output enable pin. See Table 3B for function. LVCMOS/LVTTL interface levels.
3	GND	Power		Power supply ground.
5, 4	FSEL1, FSEL0	Input	Pulldown	Default frequency select pins. LVCMOS/LVTTL interface levels. Refer to the FemtoClock NG Ceramic-Package XO and VCXO Ordering Product Information document for default frequency order codes.
6	Q	Output		Clock output. LVCMOS/LVTTL interface levels.
7	DNU			Do not use. Do not connect.
8	V _{DD}	Power		Positive power supply.
9	SDATA	Input	Pullup	I ² C Data Input. LVCMOS/LVTTL interface levels.
10	SCLK	Input	Pullup	I ² C Clock Input. LVCMOS/LVTTL interface levels.

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance		FSEL[1:0], SDATA, SCLK, OE		3.5		pF
			VC		10		pF
C _{PD}	Power Dissipation Capacitance		V _{DD} = 3.465V or 2.625V		8		pF
R _{PULLUP}	Input Pullup Resistor				50		kΩ
R _{PULLDOWN}	Input Pulldown Resistor				50		kΩ
R _{OUT}	Output Impedance	Q	V _{DD} = 3.3V		15		Ω
			V _{DD} = 2.5V		19		Ω

Function Tables

Table 3A. Default Frequency Selection

Input		Operation
FSEL1	FSEL0	
0 (default)	0 (default)	Default frequency 0.
0	1	Default frequency 1.
1	0	Default frequency 2.
1	1	Default frequency 3.

NOTE: The default frequency is the output frequency after power-up. One of four default frequencies is selected by FSEL[1:0]. See programming section for details.

Table 3B. OE Configuration

Input	Output Enable
OE	
0	Output Q are in high-impedance state.
1 (default)	Outputs are enabled.

NOTE: OE is an asynchronous control.

Principles of Operation

The block diagram consists of the internal 3rd overtone crystal and oscillator which provide the reference clock f_{XTAL} of 114.285MHz. The PLL includes the FemtoClock NG VCO along with the pre-divider (P), the feedback divider (M) and the post divider (N). The P , M , and N dividers determine the output frequency based on the f_{XTAL} reference and must be configured correctly for proper operation. The feedback divider is fractional supporting a huge number of output frequencies. The configuration of the feedback divider to integer-only values results in an improved output phase noise characteristics at the expense of the range of output frequencies. In addition, internal registers are used to hold up to four different factory pre-set P , M , and N configuration settings. These default pre-sets are stored in the I²C registers at power-up. Each configuration is selected via the FSEL[1:0] pins and can be read back using the SCLK and SDATA pins.

The user may choose to operate the device at an output frequency different than that set by the factory. After power-up, the user may write new P , N and M settings into one or more of the four configuration registers and then use the FSEL[1:0] pins to select the newly programmed configuration. Note that the I²C registers are volatile and a power supply cycle will reload the pre-set factory default conditions.

If the user does choose to write a different P , M , and N configuration, it is recommended to write to a configuration which is not currently selected by FSEL[1:0] and then change to that configuration after the I²C transaction has completed. Changing the FSEL[1:0] controls results in an immediate change of the output frequency to the selected register values. The P , M , and N frequency configurations support an output frequency range 15.476MHz to 260MHz.

The devices use the fractional feedback divider with a delta-sigma modulator for noise shaping and robust frequency synthesis capability. The relatively high reference frequency minimizes phase noise generated by frequency multiplication and allows more efficient shaping of noise by the delta-sigma modulator.

The output frequency is determined by the 2-bit pre-divider (P), the feedback divider (M) and the 7-bit post divider (N). The feedback divider (M) consists of both a 7-bit integer portion ($MINT$) and an 18-bit fractional portion ($MFRAC$) and provides the means for high-resolution frequency generation. The output frequency f_{OUT} is calculated by:

$$f_{OUT} = f_{XTAL} \cdot \frac{1}{P \cdot N} \cdot \left[MINT + \frac{MFRAC + 0.5}{2^{18}} \right] \quad (1)$$

The four configuration registers for the P , M ($MINT$ & $MFRAC$) and N dividers which are named Pn , $MINTn$, $MFRACn$ and Nn with $n = 0$ to 3. “n” denominates one of the four possible configurations.

As identified previously, the configurations of P , M ($MINT$ & $MFRAC$) and N divider settings are stored the I²C register, and the configuration loaded at power-up is determined by the FSEL[1:0] pins.

Table 4. Frequency Selection

Input		Selects	Register
FSEL1	FSEL0		
0 (def.)	0 (def.)	Frequency 0	P0, MINT0, MFRAC0, N0
0	1	Frequency 1	P1, MINT1, MFRAC1, N1
1	0	Frequency 2	P2, MINT2, MFRAC2, N2
1	1	Frequency 3	P3, MINT3, MFRAC3, N3

Frequency Configuration

An order code is assigned to each frequency and VCXO pull range configuration programmed by the factory (default frequencies). For available order codes, see the *FemtoClock NG Ceramic-Package XO and VCXO Ordering Product Information* document.

For more information and guidelines on programming of the device for custom frequency configurations, programming for a specific VCXO pull range, the available APR (absolute pull range), the register description and the serial interface description, see the *FemtoClock NG Ceramic 5x7 Module Programming Guide*.

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of the product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V_{DD}	3.6V
Inputs, V_I	-0.5V to $V_{DD} + 0.5V$
Outputs, I_O (LVCMOS)	-0.5V to $V_{DD} + 0.5V$
Outputs, I_O (SDATA)	10mA
Package Thermal Impedance, θ_{JA}	49.4°C/W (mps)
Storage Temperature, T_{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 5A. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Supply Voltage		3.135	3.3	3.465	V
I_{DD}	Power Supply Current	No Load, OE = Low		135	150	mA

Table 5B. Power Supply DC Characteristics, $V_{DD} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Supply Voltage		2.375	2.5	2.625	V
I_{DD}	Power Supply Current	No Load, OE = Low		130	145	mA

Table 5C. LVCMOS/LVTTL DC Characteristic, $V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage	OE, SCLK, SDATA, FSEL[1:0]	$V_{DD} = 3.3V$	2		$V_{DD} + 0.3$	V
			$V_{DD} = 2.5V$	1.7		$V_{DD} + 0.3$	V
V_{IL}	Input Low Voltage	OE, SCLK, SDATA, FSEL[1:0]	$V_{DD} = 3.465V$	-0.3		0.8	V
			$V_{DD} = 2.5V$	-0.3		0.7	V
I_{IH}	Input High Current	OE,	$V_{DD} = V_{IN} = 3.465V$ or $2.625V$			10	μA
		SDATA, SCLK	$V_{DD} = V_{IN} = 3.465V$ or $2.625V$			5	μA
		FSEL0, FSEL1	$V_{DD} = V_{IN} = 3.465V$ or $2.625V$			150	μA
I_{IL}	Input Low Current	OE	$V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$	-500			μA
		SDATA, SCLK	$V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$	-150			μA
		FSEL0, FSEL1	$V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$	-5			μA
V_{OH}	Output High Voltage	Q	$V_{DD} = 3.465V$	2.4			V
			$V_{DD} = 2.625$	1.7			V
V_{OL}	Output Low Voltage	Q	$V_{DD} = 3.6V$ or 2.625			0.4	V

AC Electrical Characteristics

Table 6A. AC Characteristics, $V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{OUT}	Output Frequency Q, nQ	$P = 1, N = 10 \dots 126$	15.476		260	MHz
f_I	Initial Accuracy	Measured at $25^{\circ}C$ at Final Test			± 10	ppm
f_S	Temperature Stability	Option code = A or B			± 100	ppm
		Option code = E or F			± 50	ppm
		Option code = K or L			± 20	ppm
f_A	Aging	Frequency drift over 10 year life			± 3	ppm
		Frequency drift over 15 year life			± 5	ppm
f_T	Total Stability	Option code A or B (10 year life)			± 113	ppm
		Option code E or F (10 year life)			± 63	ppm
		Option code K or L (10 year life)			± 33	ppm
$\eta_{jit(cc)}$	Cycle-to-Cycle Jitter; NOTE 1	$V_{DD} = 3.3V$		15	32	ps
		$V_{DD} = 2.5V$		18	40	ps
$\eta_{jit(per)}$	Period Jitter; NOTE 1	$V_{DD} = 3.3V$		2.6	5	ps
		$V_{DD} = 2.5V$		4	7	ps
$\eta_{jit(\emptyset)}$	RMS Phase Jitter (Random)	$17MHz \leq f_{out} \leq 260MHz$, Integration Range: 12kHz - 20MHz; NOTE 3		0.70	1.20	ps
		156.25MHz, Integration Range: 12kHz - 20MHz; NOTE 2		0.64	0.92	ps
		156.25MHz, Integration Range: 1kHz - 40MHz		0.85	1.00	ps
$\Phi_N(100)$	Single-side band phase noise, 100Hz from Carrier	156.25MHz		-75		dBc/Hz
$\Phi_N(1k)$	Single-side band phase noise, 1kHz from Carrier	156.25MHz		-98		dBc/Hz
$\Phi_N(10k)$	Single-side band phase noise, 10kHz from Carrier	156.25MHz		-118		dBc/Hz
$\Phi_N(100k)$	Single-side band phase noise, 100kHz from Carrier	156.25MHz		-127		dBc/Hz
$\Phi_N(1M)$	Single-side band phase noise, 1MHz from Carrier	156.25MHz		-139		dBc/Hz
$\Phi_N(10M)$	Single-side band phase noise, 10MHz from Carrier	156.25MHz		-143		dBc/Hz
t_R / t_F	Output Rise/Fall Time	$V_{DD} = 3.3V$, 20% to 80%	150	425	700	ps
		$V_{DD} = 2.5V$, 20% to 80%	150	500	800	ps
odc	Output Duty Cycle		45	50	55	%
t_{OSC}	Oscillator Start-Up Time				20	ms
t_{SET}	Output frequency settling time after FSEL0 and FSEL1 values are changed				1	ms

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: All AC parameters are characterized with $P = 1$.

NOTES continued on next page.

NOTE: Please see the FemtoClock Ceramic 5x7 Modules Programming Guide for more information on PLL feedback modes and the optimum configuration for phase noise.

NOTE 1: This parameter is defined in accordance with JEDEC standard 65.

NOTE 2: Please refer to the phase noise plots.

NOTE 3: Applies to output frequencies: 17MHz, 19.44MHz, 25MHz, 33.33MHz, 75MHz, 77.76MHz, 100MHz, 106.25MHz, 122.88MHz, 125MHz, 150MHz, 155.52MHz, 156.25MHz, 161.132MHz, 175MHz, 187.5MHz, 200MHz, 212.5MHz, 250MHz and 260MHz.

Table 6B. VCXO Control Voltage Input (V_C) Characteristics,

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
K_V	Oscillator Gain, NOTE 1, 2, 3	$V_{DD} = 3.3V$	7.57		477.27	ppm/V
		$V_{DD} = 2.5V$	10		630	ppm/V
L_{VC}	Control Voltage Linearity; NOTE 4	BSL Variation	-5	± 0.4	+5	%
BW	Modulation Bandwidth			100		kHz
Z_{VC}	VC Input Impedance			500		k Ω
$V_{C_{NOM}}$	Nominal Control Voltage			$V_{DD}/2$		V
V_C	Control Voltage Tuning Range; NOTE 4	$V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$	0		V_{DD}	V

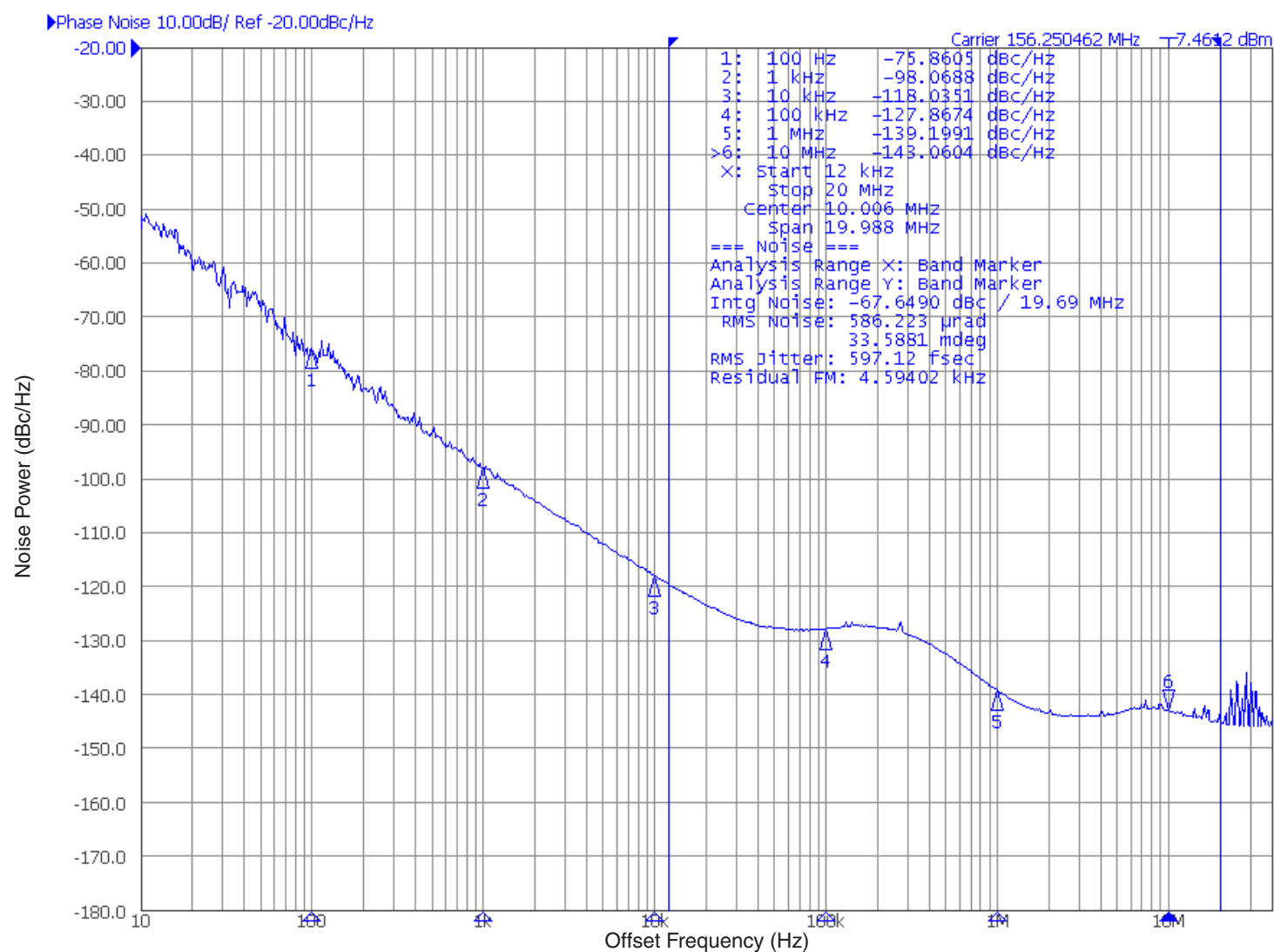
NOTE 1: $V_C = 0V$ to V_{DD} . Oscillator gain is programmed by IDT. Gain = $(25 \cdot n) \div V_{CC}$ and is in the range of $n=1$ to $n = 63$.

NOTE 2: Nominal oscillator gain: Please refer to the FemtoClock NG Ceramic 5x7 Module Programming Guide document.

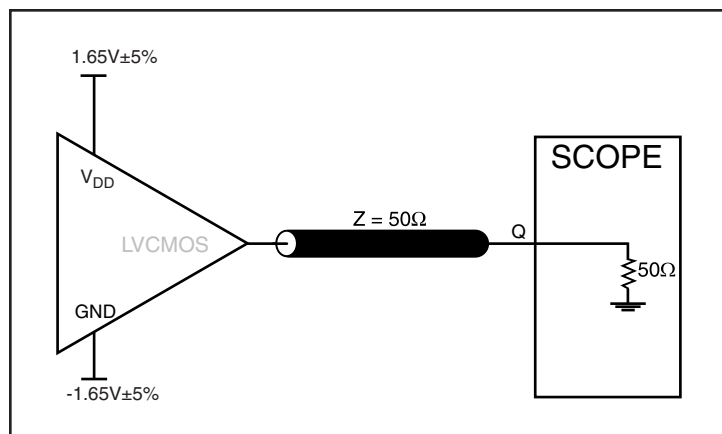
NOTE 3: For best phase noise performance, use the lowest K_V that meets the requirements of the application.

NOTE 4: BSL = Best Straight Line Fit: Variation of the output frequency vs. control voltage V_C , in percent. V_C ranges from 10% to 90% V_{DD} .

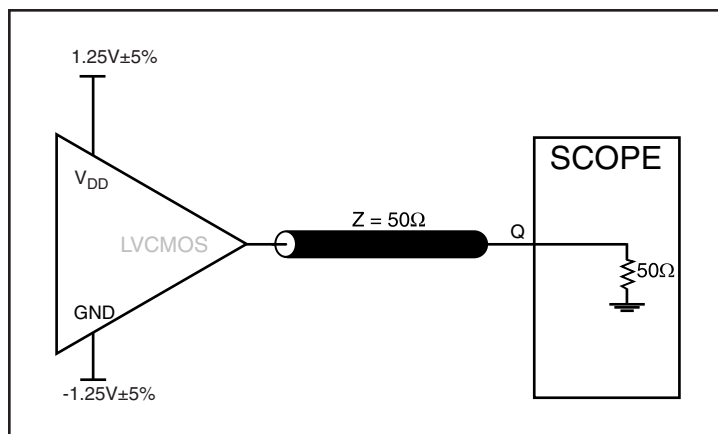
Typical Phase Noise at 156.25MHz (12kHz - 20MHz)



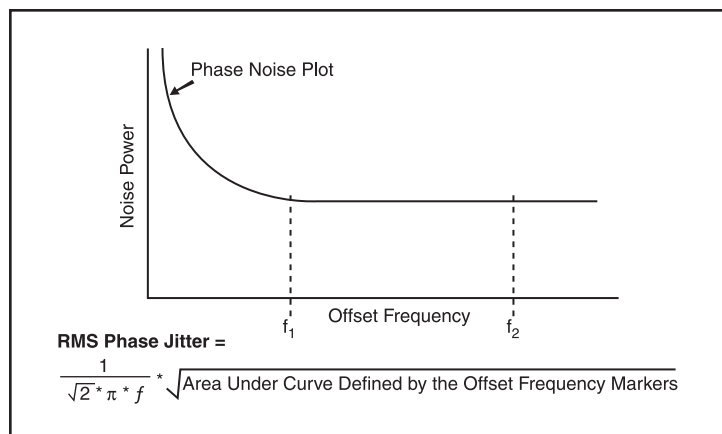
Parameter Measurement Information



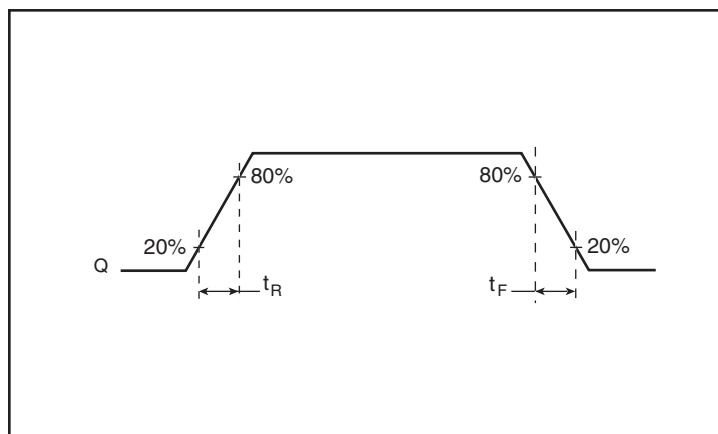
3.3V LVC MOS Output Load Test Circuit



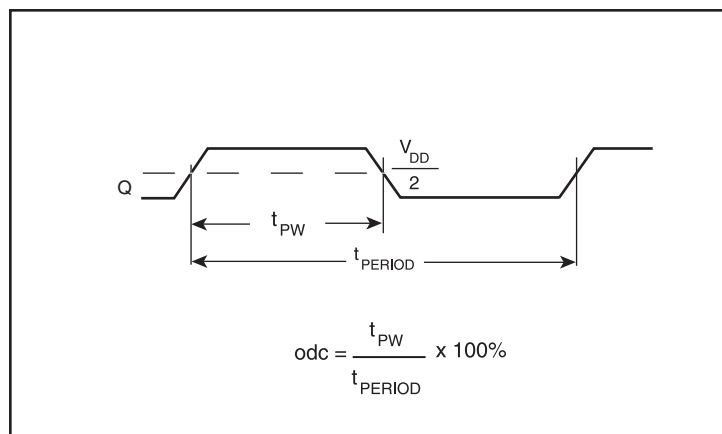
2.5V LVC MOS Output Load Test Circuit



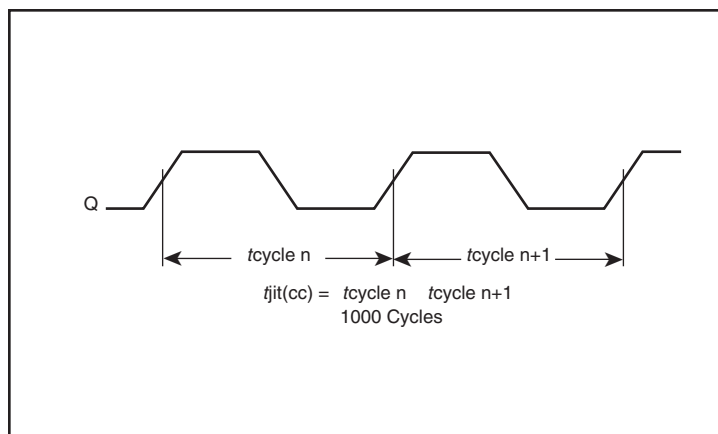
RMS Phase Jitter



Output Rise/Fall Time

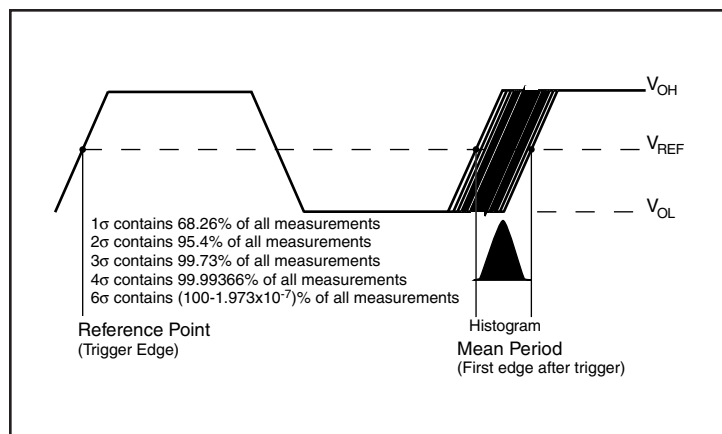


Output Duty Cycle/Pulse Width/Period



Cycle-to-Cycle Jitter

Parameter Measurement Information, continued



Period Jitter

Applications Information

Recommendations for Unused Input Pins

Inputs:

LVC MOS Select Pins

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A 1k Ω resistor can be used.

Schematic Example

Figure 1 shows an example 8N0QV01 application schematic in which the device is operated at $V_{DD} = +3.3V$. The schematic example focuses on functional connections and is intended as an example only and may not represent the exact user configuration. Refer to the pin description and functional tables in the datasheet to ensure the logic control inputs are properly set. For example OE and FSEL[1:0] can be configured from an FPGA instead of set with pull up and pull down resistors as shown.

The 8N0QV01 is not a self contained part; it requires pairing with a PLL. The two connections necessary to be made to the PLL are VC, the analog control voltage that sets the center frequency of the VCXO, and Q, which is the oscillator output. VC is the analog output of the PLL low pass loop filter that serves to remove noise from the phase detector error output.

As with any high speed analog circuitry, the power supply pins are vulnerable to random noise, so to achieve optimum jitter performance isolation of the V_{DD} pin from the power supply is required. In order to

achieve the best possible filtering, it is recommended that the placement of the filter components be on the device side of the PCB as close to the power pins as possible. If space is limited, the $0.1\mu F$ capacitor on the V_{DD} pin must be placed on the device side with direct return to the ground plane through vias. The remaining filter components can be on the opposite side of the PCB.

Power supply filter component recommendations are a general guideline to be used for reducing external noise from coupling into the devices. The filter performance is designed for a wide range of noise frequencies. This low-pass filter starts to attenuate noise at approximately 10kHz. If a specific frequency noise component is known, such as switching power supplies frequencies, it is recommended that component values be adjusted and if required, additional filtering be added. Additionally, good general design practices for power plane voltage stability suggests adding bulk capacitance in the local area of all devices.

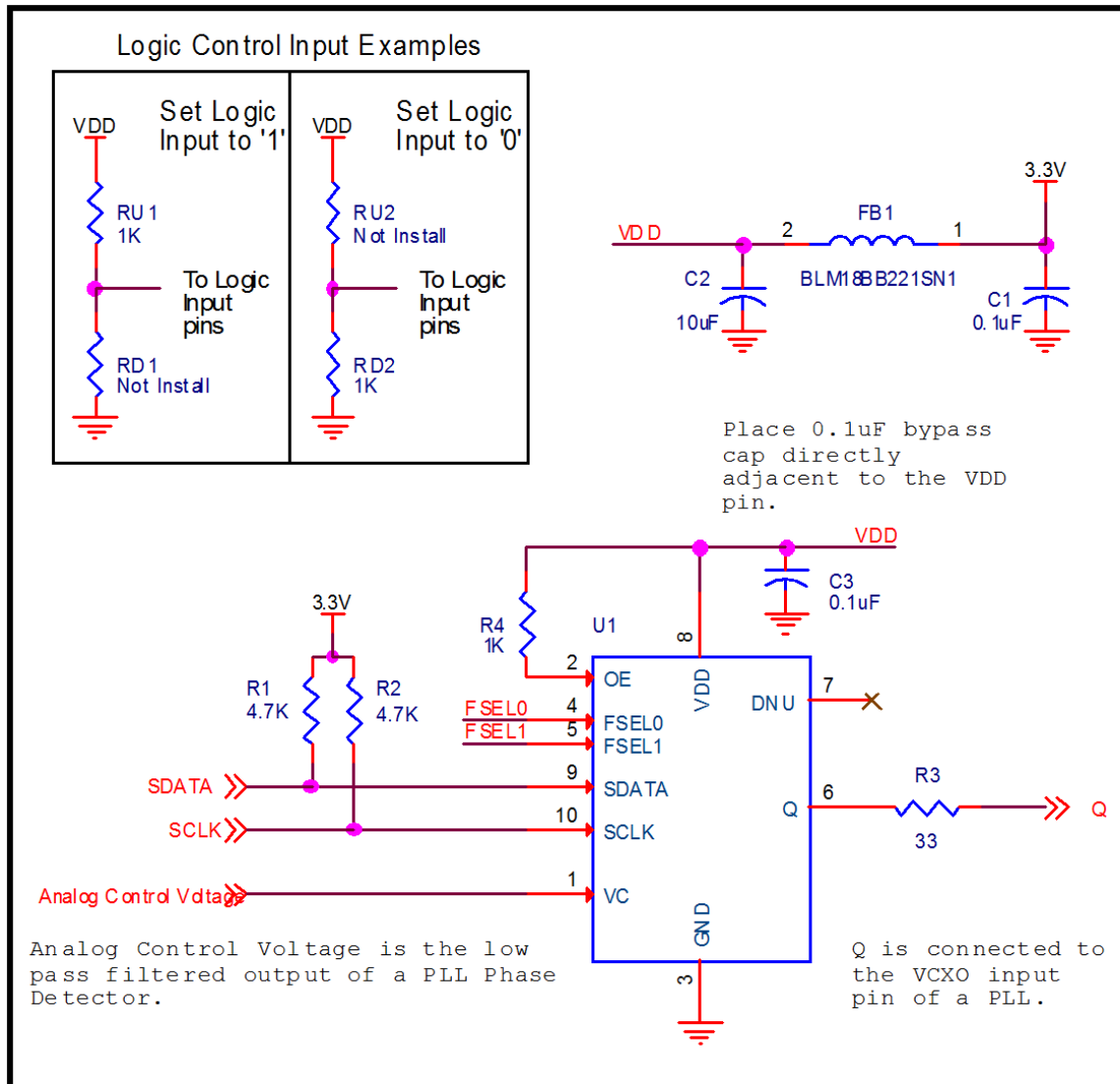


Figure 1. IDT8N0QV01 Schematic Example

Power Considerations

This section provides information on power dissipation and junction temperature for the IDT8N0QV01. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the IDT8N0QV01 is the sum of the core power plus the power dissipation in the load(s). The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

- Power (core)_{MAX} = $V_{DD_MAX} * I_{DD} = 3.465V * 150mA = 519.8mW$

Total Static Power:

$$= \text{Power (core)}_{MAX} = 519.8mW$$

Dynamic Power Dissipation at $F_{OUT} \text{ (max)}$

$$\text{Total Power (} F_{OUT_MAX} \text{)} = [(C_{PD} * N) * \text{Frequency} * (V_{DD})^2] = [(8pF * 1) * 260MHz * (3.465V)^2] = 24.97mW$$

Total Power

$$\begin{aligned} &= \text{Static Power} + \text{Dynamic Power Dissipation} \\ &= 519.8mW + 24.97mW \\ &= 544.77mW \end{aligned}$$

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad, and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 49.4°C/W per Table 7 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ C + 0.545W * 49.4^\circ C/W = 112^\circ C. \text{ This is below the limit of } 125^\circ C.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 7. Thermal Resistance θ_{JA} for a 10-lead Ceramic 5mm x 7mm Package, Forced Convection

Meters per Second	θ_{JA} by Velocity		
	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	49.4°C/W	44.2°C/W	41.0°C/W

Reliability Information

Table 8. θ_{JA} vs. Air Flow Table for a 10-lead Ceramic 5mm x 7mm Package

θ_{JA} vs. Air Flow			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	49.4°C/W	44.2°C/W	41.0°C/W

Transistor Count

The transistor count for IDT8N0QV01 is: 47,302

Package Outline and Package Dimensions

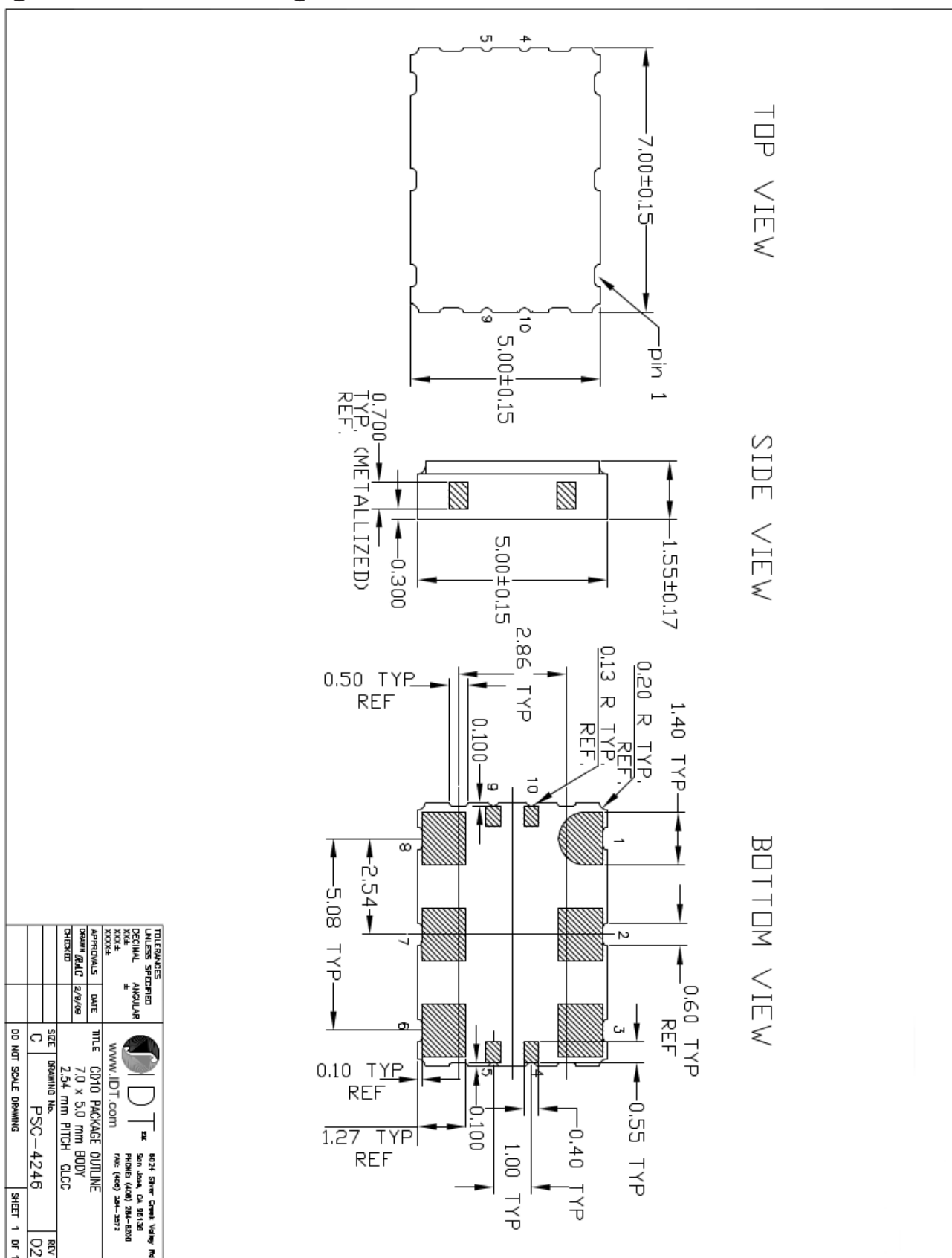


Table 9. Device Marking

Marking	Industrial Temperature Range ($T_A = -40^{\circ}\text{C}$ to 85°C)	Commercial Temperature Range ($T_A = 0^{\circ}\text{C}$ to 70°C)
	IDT8N0QV01yH- ddddCDI	IDT8N0QV01yH- ddddCD
	y = Option Code, dddd=Default-Frequency and VCXO Pull Range	

NOTE: For available order codes, see the FemtoClock NG Ceramic-Package XO and VCXO Ordering Product Information document.

For more information and guidelines on programming of the device for custom frequency configurations, programming for a specific VCXO pull range, the available APR (absolute pull range), the register description and the serial interface description, see the FemtoClock NG Ceramic 5x7 Module Programming Guide.

Revision History Sheet

Rev	Table	Page	Description of Change	Date
A	T1	3	first row: deleted '(see Table 3C).'	3/14/2014
			forth row: replaced description.	
	6A	8	Deleted NOTE 2 from RMS Phase Jitter. Added 'NOTE 2' to 156.25MHz.	
	6B	9	Note 2: Added 'Please refer to the FemtoClock NG Ceramic 5x7 Module Programming Guide document.'	
		14	Power Considerations. Changed Dynamic Power Dissipation from 2.5mW to 24.97mW	

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